

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMG1013UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

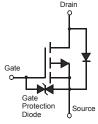
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



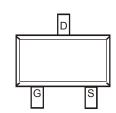








Fauivalent Circuit



Ton View

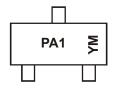
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1013UWQ-7	SOT323	3000 / Tape & Reel
DMG1013UWQ-13	SOT323	10000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PA1 = Product Type Marking Code YM or YM = Date Code Marking Y or Y= Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Kev

Year	2008		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V		ı	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteris	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-20	V		
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 5)	I _D	-0.82 -0.54	Α		
Pulsed Drain Current (Note 6)	I _{DM}	-3	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)		P _D	0.31	W
Thermal Resistance, Junction to Ambient	@T _A = +25°C (Note 5)	$R_{ heta JA}$	398	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

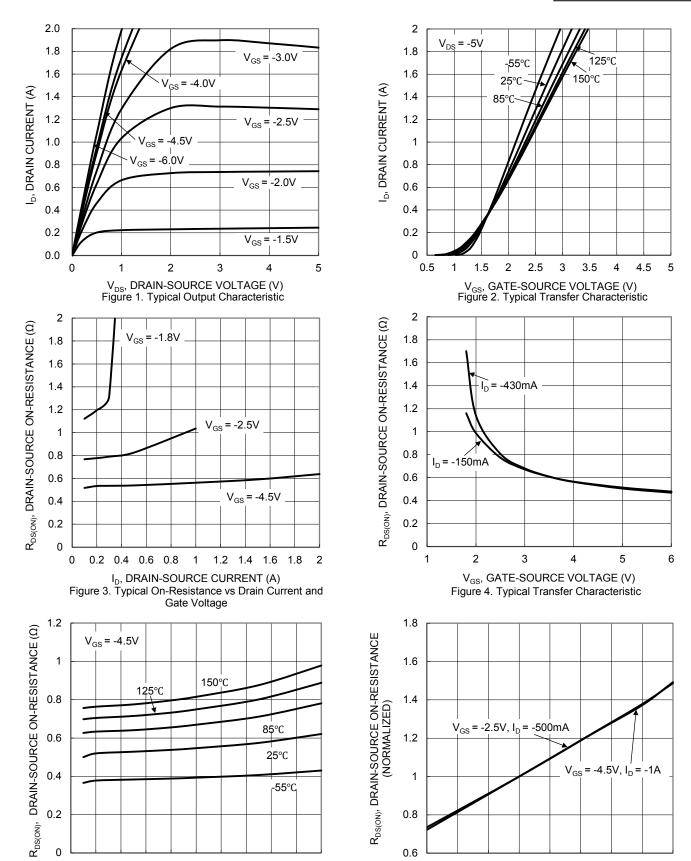
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$			
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	ı	-	-100	nA	V _{DS} = -20V, V _{GS} = 0V			
Gate-Source Leakage	I _{GSS}	-	-	±2.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$			
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$			
			0.5	0.75		$V_{GS} = -4.5V$, $I_D = -430mA$			
Static Drain-Source On-Resistance	R _{DS(ON)}	-	0.7	1.05	Ω	$V_{GS} = -2.5V$, $I_D = -300$ mA			
			1.0	1.5		$V_{GS} = -1.8V, I_D = -150mA$			
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V$, $I_{D} = -250$ mA			
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C _{iss}	ı	59.76	ı	pF				
Output Capacitance	Coss	ı	12.07	ı	pF	V _{DS} = -16V, V _{GS} = 0V, f = 1.0MHz			
Reverse Transfer Capacitance	C _{rss}	1	6.36	-	pF	1 - 1.000112			
Total Gate Charge	Q_g	-	622.4	-	рC	4.577.77			
Gate-Source Charge	Q_{gs}	-	100.3	-	рC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -250$ mA			
Gate-Drain Charge	Q_{gd}	-	132.2	-	рС	1D = -23011IA			
Turn-On Delay Time	t _{D(ON)}	-	5.1	-	ns				
Turn-On Rise Time	t _R	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$			
Turn-Off Delay Time	t _{D(OFF)}	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $I_D = -200\text{mA}$			
Turn-Off Fall Time	tϝ	-	20.7	-	ns	TID ZOOTIA			

Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.





I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature

1

1.2 1.4 1.6 1.8

50

75

100

25

0

0

0.2 0.4 0.6 0.8

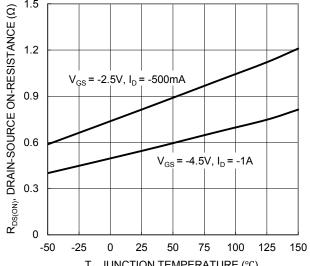
0.6

-50

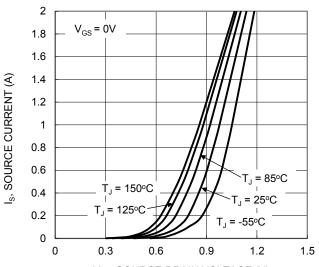
-25

125

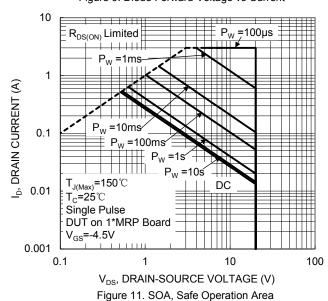




T_J, JUNCTION TEMPERATURE (°C) Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs Current



1.2 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 1 $I_D = -1mA$ 8.0 $I_D = -250 \mu A$ 0.6 0.4 -50 -25 0 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs Junction Temperature

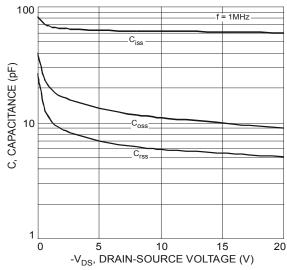


Figure 10. Typical Total Capacitance



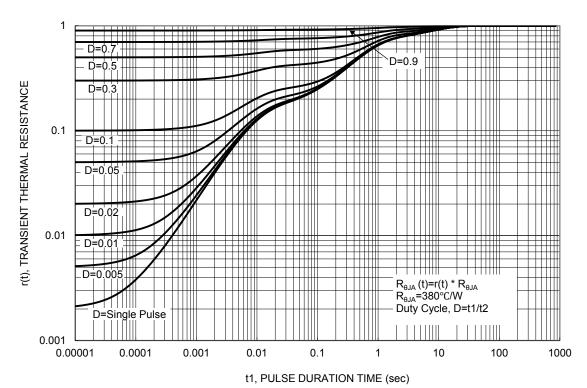


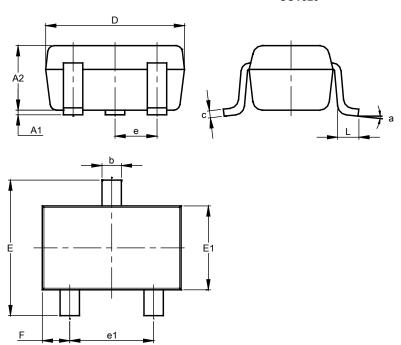
Figure 12. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

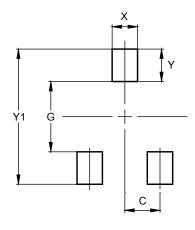


SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	0.650 BSC					
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	8°						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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